

## Features

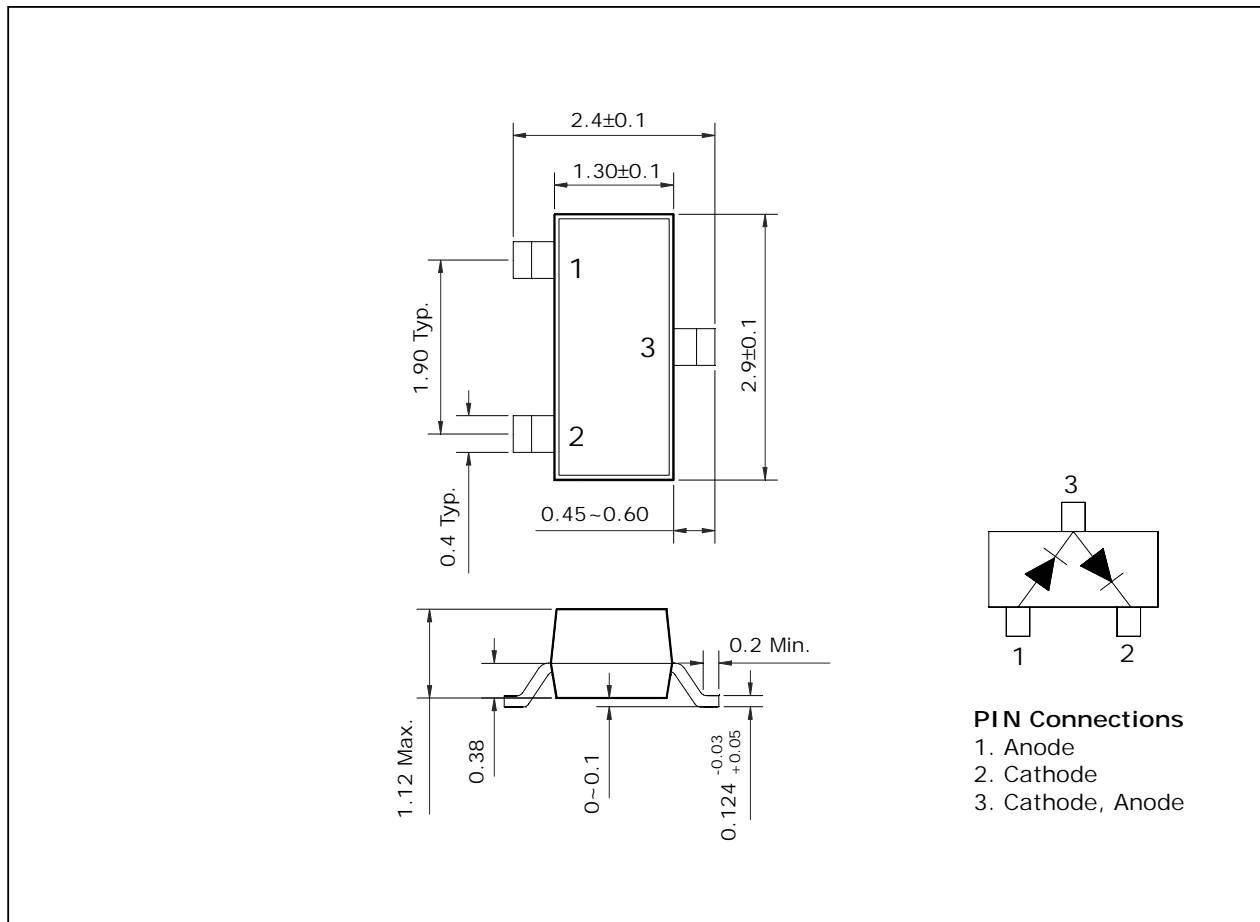
- Low power rectified
- Silicon epitaxial type
- High reliability

## Ordering Information

Type No.	Marking	Package Code
SDB310WM	DB3	SOT-23

## Outline Dimensions

unit : mm



# SDB310WM

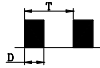
## Absolute maximum ratings

Ta=25°C

Characteristic	Symbol	Ratings	Unit
Reverse voltage	V <sub>R</sub>	30	V
Repetitive peak forward current	I <sub>FRM</sub> *	0.5	A
Forward current	I <sub>F</sub>	0.2	A
Non-repetitive peak forward current(10ms)	I <sub>FSM</sub>	2	A
Power dissipation	P <sub>D</sub>	150	mW
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 ~ 150	°C

\* :  $\delta = D/T = 0.33$

(T<1S)



\* : Unit ratings. Total rating=Unit rating×1.5

## Electrical Characteristics

Ta=25°C

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward voltage 1	V <sub>F(1)</sub>	I <sub>F</sub> =10mA	-	-	0.4	V
Forward voltage 2	V <sub>F(2)</sub>	I <sub>F</sub> =30mA	-	-	0.5	V
Reverse current	I <sub>R</sub>	V <sub>R</sub> =30V	-	-	1	μA
Total capacitance	C <sub>T</sub>	V <sub>R</sub> =1V, f=1MHz	-	-	10	pF
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = I <sub>R</sub> =10mA, I <sub>RR</sub> = 1mA, R <sub>L</sub> =100Ω	-	-	5	ns

Electrical Characteristic Curves

Fig. 1  $I_F - V_F$

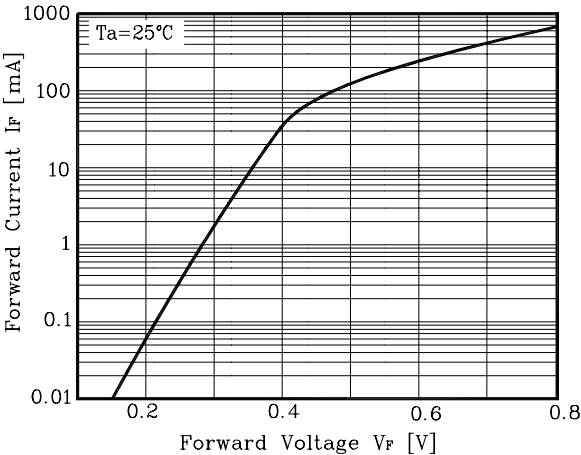


Fig. 2  $I_R - V_R$

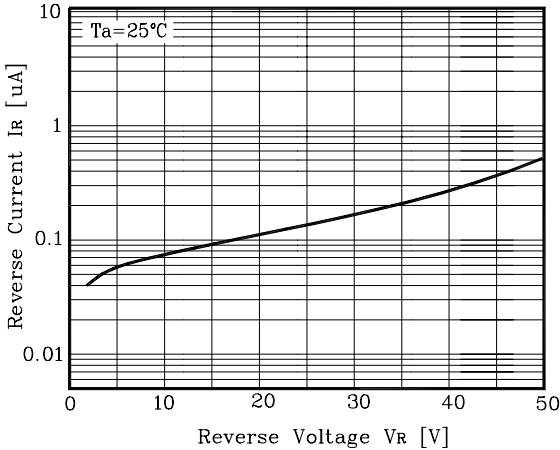


Fig. 3  $C_T - V_R$

